

ABSTRACT

The present invention pertains to a reflective mask blank for EUV lithography in which a multilayer reflective film for reflecting EUV light and a phase shift film for shifting the phase of the EUV light are formed in the sequence listed on a substrate, the phase shift film having a layer 1 containing ruthenium (Ru) and nitrogen (N), and the absolute value of the film stress of the layer 1 is 1000 MPa or below.

Fig 1